PATENT

IN THE UNITED STATES PATENT OFFICE

Applicant:	Kevin T. Look		
Assignee:	Xilinx, Inc.		
Title:	"Low Voltage Non-Volatile Memory Cell"		
Serial No.:	Not Yet Known	File Date:	10-24-03
Examiner:	Not Yet Known	Art Unit:	Not Yet Known
Divisional of Serial No.:	10/283,736	File Date:	10-29-02
Docket No.:	X-719-1D-3D US		

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INFORMATION DISCLOSURE STATEMENT

Dear Sir:

Pursuant to 37 C.F.R. 1.56, Applicant brings to the attention of the Examiner the twenty-two (22) references listed in the attached Substitute for Form PTO-1449 (Information Disclosure Statement by Applicant).

All of these references were cited in prior related U.S. patent application Serial Number 10/283,736 filed October 29, 2002 to which this application claims priority. Copies of these references have not been supplied herein since they were previously submitted in the parent case.

Citation of the above documents shall not be construed as an admission that the documents are necessarily prior art with respect to the instant invention. Citation of the above documents shall not be construed as a representation that a search has been made other than as described above. Also, the citation of the above documents shall not be construed as an admission that the information cited herein is, or is considered to be, material to patentability as defined in §1.56(b).

Respectfully Submitted,

Lois D. Cartier
Agent for Applicant
Reg. No. 40,941

LDC:pbs

pbs

PTO/SB/08A (10-01)
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Patent and Trademark Office: U.S. DEPARTMENT OF COMMERCE
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Substitute for form 1449A/PTO

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(use as many sheets as necessary)

Sheet 1 of 2

Complete if Known	
Application / Conf. No.	Unknown /
Filing Date	October 24, 2003
First Named Invent r	Kevin T. Look
Art Unit	Unknown
Examiner Name	Unknown
Attorney Docket Number	X-719-1D-3D US

U.S. PATENT DOCUMENTS

Examiner Initials *	Cite No.[1]	Document Number Number - Kind Code (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		US- 5,627,400	05-06-92	Koga	
		US- 5,656,528	08-12-97	Wahlstrom	
		US- 5,821,160	10-13-98	Rodriguez et al.	
		US- 5,972,756	10-26-99	Kono et al.	
		US- 6,235,574 B1	05-22-01	Tobben et al	
		US- 6,261,964 B1	07-17-01	Wu et al.	
		US- 6,495,424B1	12-17-02	Kunikiyo	
		US- 6,496,416 B1	12-17-02	Look	
		US- 2002/0022326 A1	02-21-02	Kunikiyo	
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FOREIGN PATENT DOCUMENTS

Examiner Initials *	Cite No.[1]	Foreign Patent Document Country Code [3] -Number [4] -Kind Code [5] (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T [6]
		JP 360009160 A	01-18-85	Matsushita Electric		
		JP 363079377 A	04-09-88	Oki Electric		
		JP 406163906 A	06-10-94	Sanyo Electric		
		JP 406232389 A	08-19-94	Kou		
		JP 408264660 A	10-11-96	NEC Corp.		
		JP 2000077356 A	03-14-00	Texas Instr.		

Examiner Signature		Date Considered	

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

[1] Applicant's unique citation designation number (optional). [2] See Kinds of USPTO Patent Documents at www.uspto.gov or MPEP 901.04. [3] Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). [4] For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. [5] Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. [6] Applicant is to place a check mark here if English language Translation is attached.

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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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Sheet 2 of 2

Complete if Known	
Application / Conf. No.	Unknown /
Filing Date	October 24, 2003
First Named Inventor	Kevin T. Look
Art Unit	Unknown
Examiner Name	Unknown
Attorney Docket Number	X-719-1D-3D US

OTHER -- NON PATENT LITERATURE DOCUMENTS

Examiner Initials *	Cite No.[1]	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T [2]
		"Boron Diffusion And Penetration In Ultrathin Oxide With Poly-Si Gate"; Cao et al.; IEEE Electron Device Letters; Vol. 19; No. 8; August 1998; pp. 291-293.	
		Aoyama et al.; "Flat-band Voltage Shifts In P-MOS Devices Caused By Carrier Activation In P+-Polycrystalline Silicon and Boron Penetration"; 1997 IEEE; pp. 26.1.1 - 26.1.4.	
		Alavi et al.; "A PROM Element Based On Salicide Agglomeration Of Poly Fuses In A CMOS Logic Process"; 1997 IEEE; pp. 34.3.1 - 34.3.4	
		Jang et al.; "Effects Of Thermal Processes After Silicidation On The Performance Of $TiSi_2$/Polysilicon Gate Device"; IEEE Transactions On Electron Devices; Vol. 46; No. 12; December 1999; pp. 2353 -2356.	
		Lasky et al.; "Comparison Of Transformation To Low-Resistivity Phase And Agglomeration Of $TiSi_2$ and $CoSi_2$"; IEEE Transaction On Electron Devices; Vol. 38; No. 2; February 1991; pp. 262-269.	
		Kalnitsky et al.; "$CoSi_2$ Integrated Fuses On Poly Silicon For Low Voltage 0.18 um CMOS Application"; 1999 IEEE; 4 pages.	

Examiner Signature		Date Considered	

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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